

■ PRODUCT CHARACTERISTICS

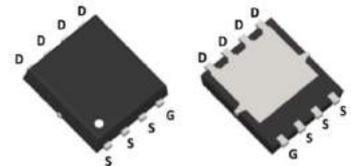
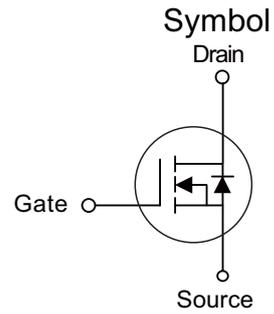
V <sub>DSS</sub>	100V
R <sub>DS(on)typ</sub> (@V <sub>GS</sub> =10 V)	11.6mΩ
R <sub>DS(on)typ</sub> (@V <sub>GS</sub> =4.5 V)	16.5mΩ
I <sub>D</sub>	38A

■ APPLICATIONS

- \* Power management in computing
- \* Load switching,quick/wireless charging
- \* Motor driving

■ FEATURES

- \* Ultra low Rdson
- \* Low gate charge
- \* Pb-free lead plating



PDFN5X6-8L

■ ORDER INFORMATION

Order codes		Package	Packing
Halogen- Free	Halogen		
N/A	MOT1514G	PDFN5X6	5000 pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS (T<sub>J</sub>=25°C Unless Otherwise Noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current	Continuous <sup>(1)</sup>	I <sub>D</sub>	38
	Pulsed <sup>(2)</sup>	I <sub>DM</sub>	154
Avalanche Energy <sup>(3)</sup>	E <sub>AS</sub>	45	mJ
Power Dissipation <sup>(4)</sup>	P <sub>D</sub>	32	W
Operating Junction Temperature	T <sub>J</sub>	-55-150	°C

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal resistance junction to ambient	θ <sub>JA</sub>	3.9	°C/W

■ ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Static characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V T <sub>J</sub> = 55°C	-	-	1.0	μA
			-	-	5.0	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.2	1.9	2.5	V
Static Drain-Source ON-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	-	11.6	14	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 15A	-	16.5	22	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 20A	-	57	-	S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V	-	0.70	1.0	V
Diode Continuous Current	I <sub>S</sub>	T <sub>C</sub> = 25°C	-	-	32	A
<b>Dynamic characteristics<sup>(5)</sup></b>						
Input Capacitance	C <sub>iSS</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 50V, f = 1MHz	-	1535	-	pF
Output Capacitance	C <sub>oss</sub>		-	335	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	8.2	-	pF
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz	-	1.9	-	Ω
<b>Switching characteristics<sup>(5)</sup></b>						
Total Gate Charge (@ V <sub>GS</sub> = 10V)	Q <sub>g</sub>	V <sub>GS</sub> = 0 to 10V V <sub>DS</sub> = 50V, I <sub>D</sub> = 20A	-	26	-	nC
Total Gate Charge (@ V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>		-	14.0	-	nC
Gate Source Charge	Q <sub>gs</sub>		-	4.3	-	nC
Gate Drain Charge	Q <sub>gd</sub>		-	6.8	-	nC
Turn-On DelayTime	t <sub>D(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 50V R <sub>L</sub> = 2.5Ω, R <sub>GEN</sub> = 6Ω	-	7.5	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	15.8	-	ns
Turn-Off DelayTime	t <sub>D(off)</sub>		-	31	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	28	-	ns
Body Diode Reverse Recovery Time	t <sub>rr</sub>		I <sub>F</sub> = 15A, dI <sub>F</sub> /dt = 100A/μs	-	43	-
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 15A, dI <sub>F</sub> /dt = 100A/μs	-	35	-	nC

**Notes:**

1. Computed continuous current assumes the condition of T<sub>J,Max</sub> while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under T<sub>J,Max</sub> = 150°C.
3. This single-pulse measurement was taken under the following condition [L = 100μH, V<sub>GS</sub> = 10V, V<sub>DS</sub> = 30V] while its value is limited by T<sub>J,Max</sub> = 150°C.
4. The power dissipation P<sub>D</sub> is based on T<sub>J,Max</sub> = 150°C.
5. This value is guaranteed by design hence it is not included in the production test.

■ TYPICAL CHARACTERISTICS

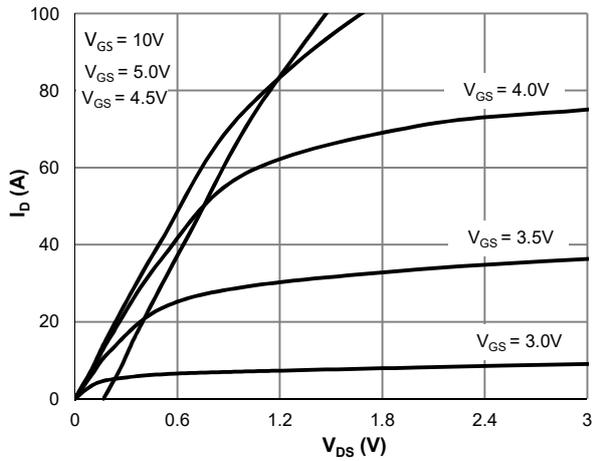


Figure 1: Saturation Characteristics

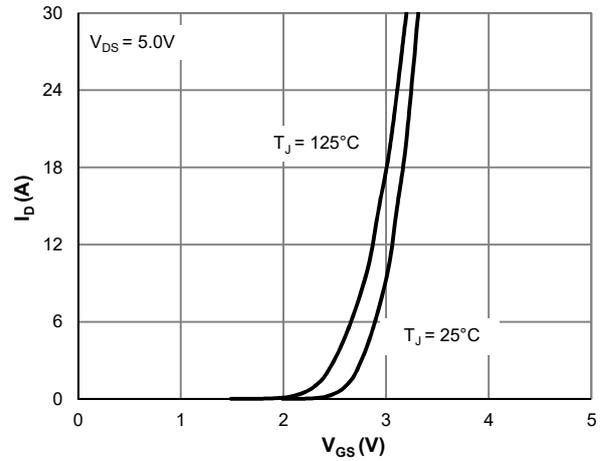


Figure 2: Transfer Characteristics

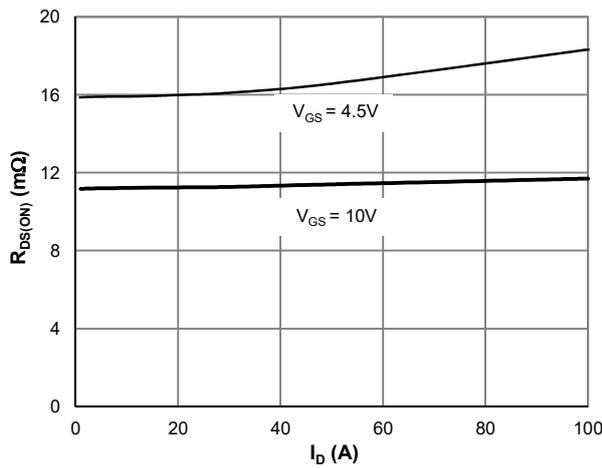


Figure 3:  $R_{DS(ON)}$  vs. Drain Current

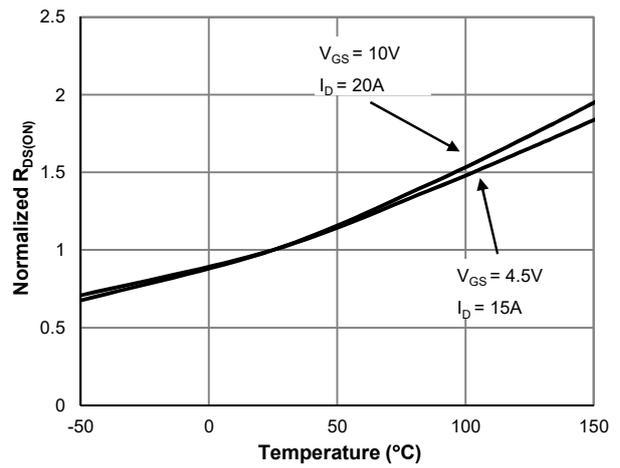


Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature

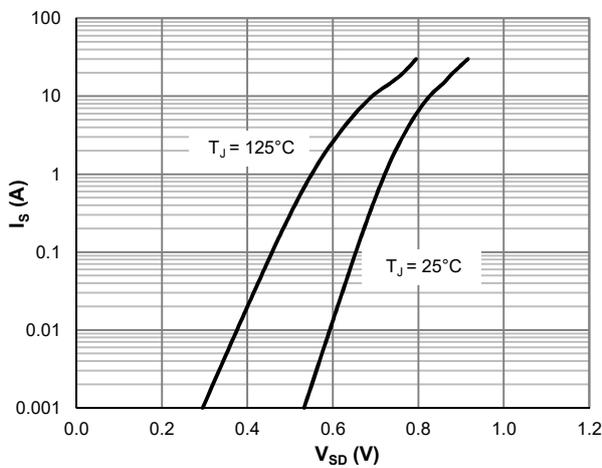


Figure 5: Body-Diode Characteristics

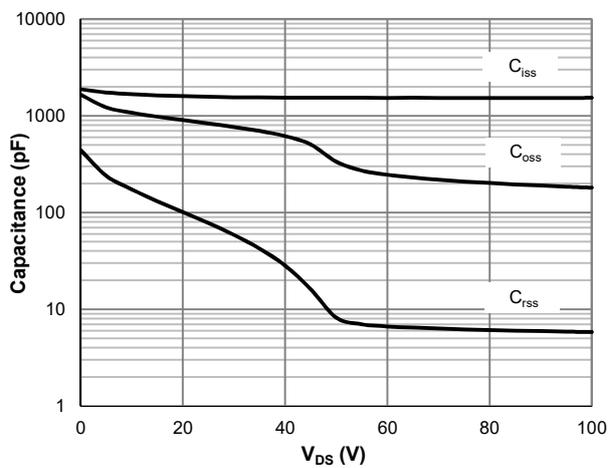


Figure 6: Capacitance Characteristics

■ TYPICAL CHARACTERISTICS(Cont.)

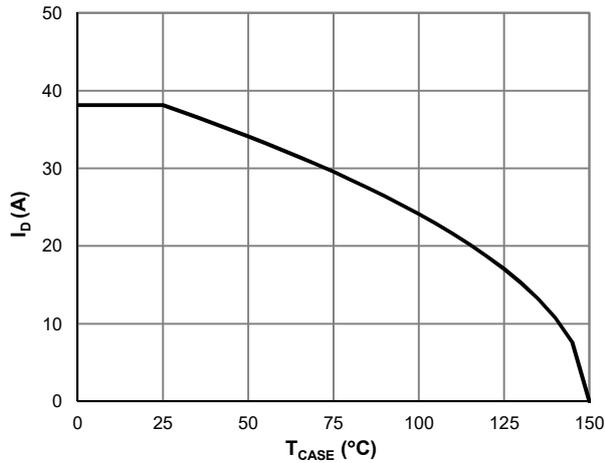


Figure 7: Current De-rating

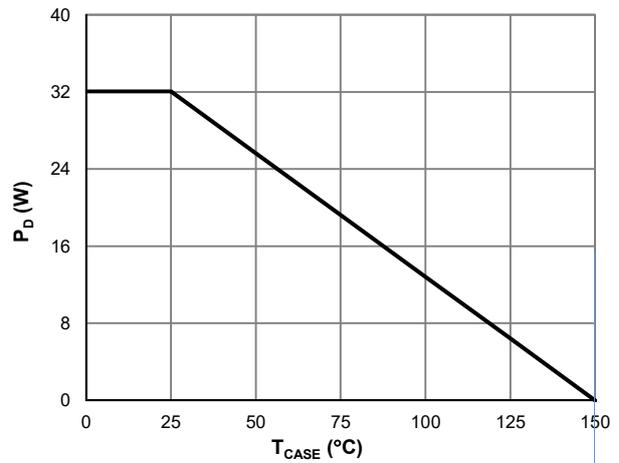


Figure 8: Power De-rating

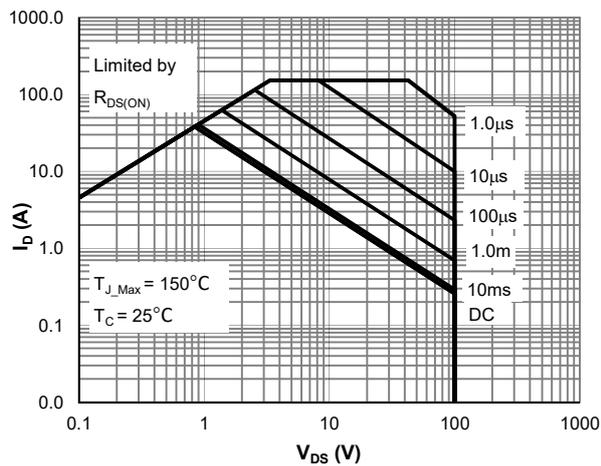


Figure 9: Maximum Safe Operating Area

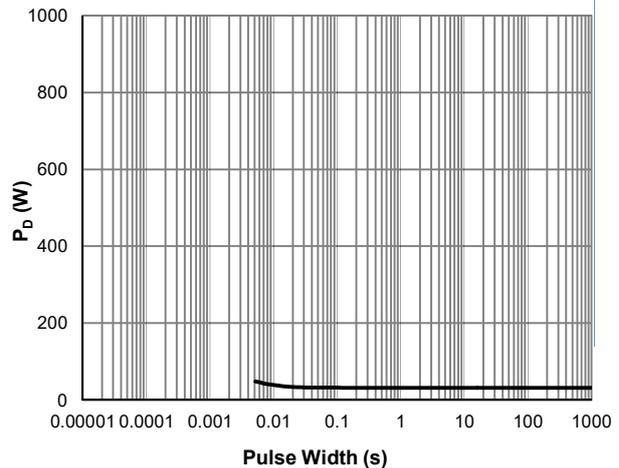


Figure 10: Single Pulse Power Rating, Junction-to-Case

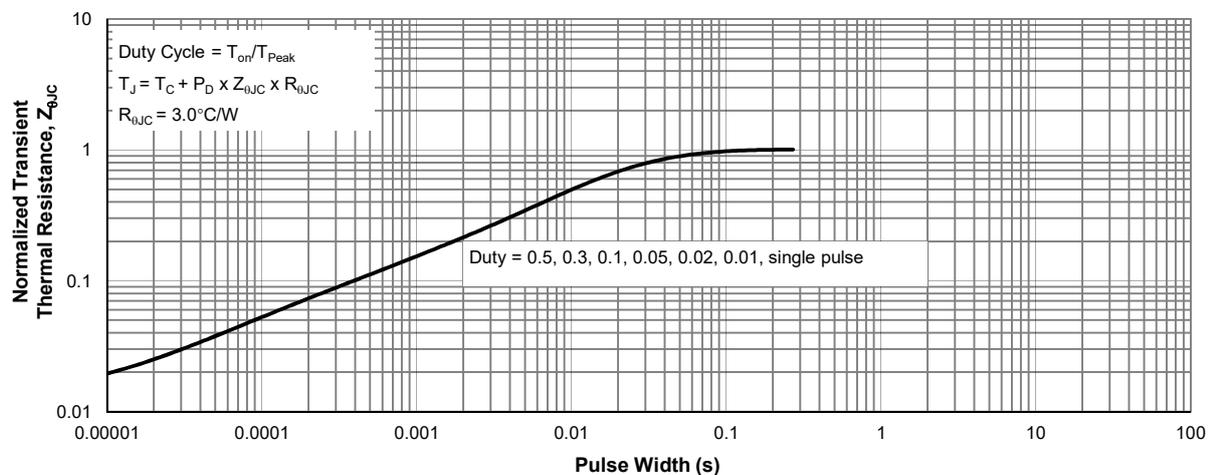
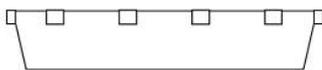
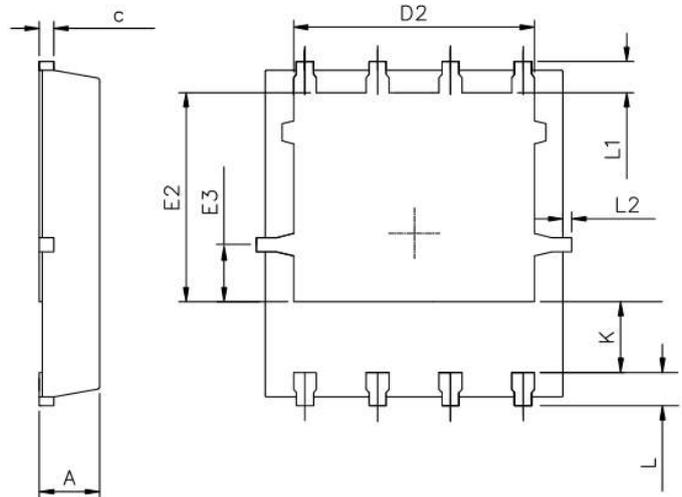
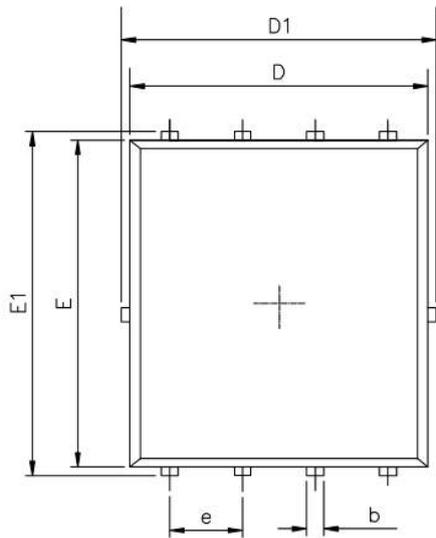
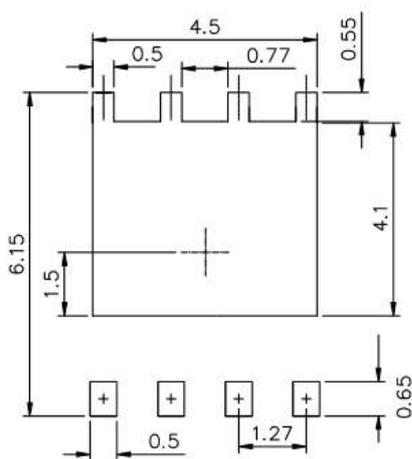


Figure 11: Normalized Maximum Transient Thermal Impedance

■ PDFN5X6-8L Package Mechanical Data



RECOMMENDED LAND PATTERN



UNIT:mm

	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50